

Low Phase Noise XO with multipliers (for 100-200MHz Fund or 3rd OT Xtal)

Universal Low Phase Noise IC's

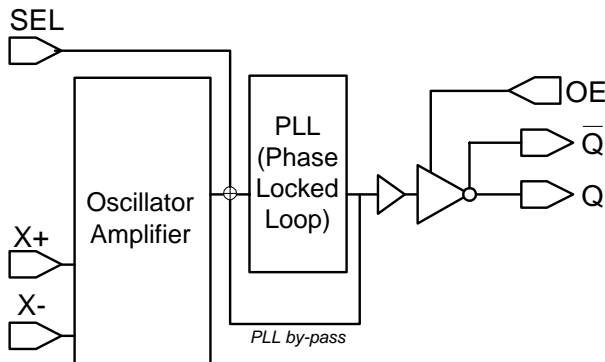
FEATURES

- 100MHz to 200MHz Fundamental or 3rd Overtone Crystal.
- Output range: 100 – 200MHz (no multiplication), 200 – 400MHz (2x multiplier), 400 – 700MHz (4x multiplier), or 800MHz-1GHz (ABX2009 only, 8x multiplier).
- CMOS (Standard drive ABX2007 or Selectable Drive ABX2006), PECL (Enable low ABX2008 or Enable high ABX2005) or LVDS output (ABX2009).
- Supports 3.3V-Power Supply.
- Available in 16-Pin (TSSOP or 3x3mm QFN)
Note: ABX2006 only available in 3x3mm.
Note: ABX2007 only available in TSSOP.

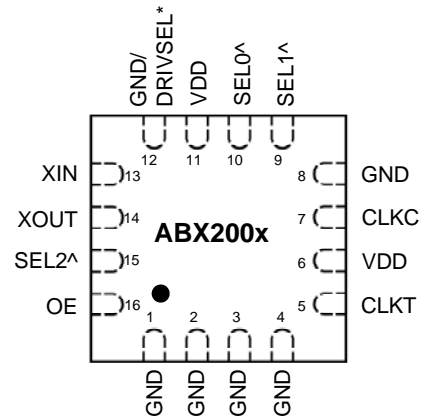
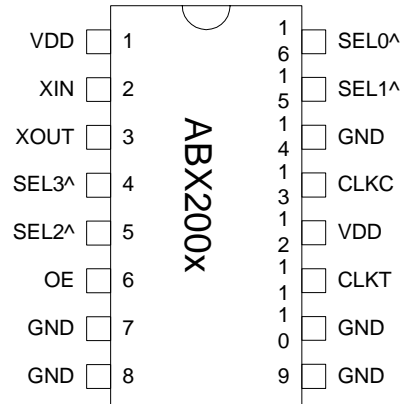
DESCRIPTION

The ABX200x family of XO IC's is specifically designed to work with high frequency fundamental and third overtone crystals. Their low jitter and low phase noise performance make them well suited for high frequency XO requirements. They achieve very low current into the crystal resulting in better overall stability.

BLOCK DIAGRAM



PIN CONFIGURATION (Top View)



^: Internal pull-up

*: ABX2006 pin 12 is output drive select (DRIVSEL)
(0 for High Drive CMOS, 1 for Standard Drive CMOS)

OUTPUT ENABLE LOGICAL LEVELS

Part #	OE	State
ABX2008	0 (Default)	Output enabled
	1	Tri-state
ABX2005 ABX2006 ABX2007 ABX2009	0	Tri-state
	1 (Default)	Output enabled

OE input: Logical states defined by PECL levels for ABX2008
Logical states defined by CMOS levels for
ABX2005/06/07/09

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PIN DESCRIPTIONS

Name	TSSOP* Pin number	3x3mm QFN* Pin number	Type	Description
VDD	1, 12	6,11	P	+3.3V power supply.
XIN	2	13	I	Crystal input. See Crystal Specification on page 3.
XOUT	3	14	I	Crystal output. See Crystal Specification on page 3.
OE	6	16	I	Output enable.
GND	7,8,9, 10, 14	1,2,3,4,8,12	P	Ground (except pin 12 on ABX2006: DRIVSEL see below).
DRIVSEL**	-	12	I	ABX2006 only: Drive Select Input. This pin has an internal pull-up that will default DRIVSEL to '1' when not connect to GND. CMOS output of ABX2006 will be high drive CMOS when DRIVSEL is set to '0', and will be standard CMOS otherwise.
CLKT	11	5	O	True output PECL (ABX2008) or LVDS (ABX2009) (N/C for ABX2007)
CLKC	13	7	O	Complementary output PECL (ABX2008) or LVDS (ABX2009) (CMOS out for ABX2007).
SEL0	16	10	I	Multiplier selector pins. These pins have an internal pull-up that will default SEL to '1' when not connected to GND.
SEL1	15	9	I	
SEL2	5	15	I	
SEL3	4	Not available	I	

* Note: ABX2006 only available in 3x3mm QFN, ABX2007 only available in TSSOP.

** Note: DRIVSEL on pin 12 on ABX2006 only.

FREQUENCY SELECTION TABLE

SEL3	SEL2	SEL1	SEL0	Selected Multiplier
0	0	1	1	Fin x 8(ABX2009 only)
1	0	1	1	Fin x 4
1	1	1	0	Fin x 2
1	1	1	1	No multiplication

Note: SEL3 is not available (always "1") in 3x3mm package

All pins have internal pull-ups (default value is 1). Connect to GND to set to 0.

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ELECTRICAL SPECIFICATIONS

1. Absolute Maximum Ratings

PARAMETERS	SYMBOL	MIN.	MAX.	UNITS
Supply Voltage	V_{DD}		4.6	V
Input Voltage, dc	V_I	-0.5	$V_{DD}+0.5$	V
Output Voltage, dc	V_O	-0.5	$V_{DD}+0.5$	V
Storage Temperature	T_S	-65	150	°C
Ambient Operating Temperature*	T_A	-40	85	°C
Junction Temperature	T_J		125	°C
Lead Temperature (soldering, 10s)			260	°C
ESD Protection, Human Body Model			2	kV

Exposure of the device under conditions beyond the limits specified by Maximum Ratings for extended periods may cause permanent damage to the device and affect product reliability. These conditions represent a stress rating only, and functional operations of the device at these or any other conditions above the operational limits noted in this specification is not implied.

* Note: Operating Temperature is guaranteed by design for all parts (COMMERCIAL and INDUSTRIAL), but tested for COMMERCIAL grade only.

2. Crystal Specifications

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Crystal Resonator Frequency	F_{XIN}	Fundamental or 3 rd overtone*	100		200	MHz
Crystal Loading Rating	$C_L (xtal)$			5		pF
Interelectrode Capacitance	C_0				5	pF
Recommended ESR	R_E	AT cut			30	Ω

* Note: 3rd overtone crystals require an external resistor between XIN and XOUT to prevent the fundamental from oscillating.

3. General Electrical Specifications

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Supply Current (Loaded Outputs)	I_{DD}	PECL/LVDS/CMOS			100/80/40	mA
Operating Voltage	V_{DD}		2.97		3.63	V
Output Clock Duty Cycle		@ 50% V_{DD} (CMOS) @ 1.25V (LVDS) @ $V_{DD} - 1.3V$ (PECL)	45	50	55	%
Short Circuit Current				±50		mA

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4. Jitter Specifications

PARAMETERS	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Period jitter RMS	At 155.52MHz, with capacitive decoupling between VDD and GND. Over 10,000 cycles		2.5		ps
Period jitter peak-to-peak			18.5	20	
Accumulated jitter RMS	At 155.52MHz, with capacitive decoupling between VDD and GND. Over 1,000,000 cycles.		2.5		ps
Accumulated jitter peak-to-peak			24	27	
Random Jitter	"RJ" measured on Wavecrest SIA 3000		2.5		ps
Integrated jitter RMS at 155MHz	Integrated 12 kHz to 20 MHz		0.3	0.4	ps
Period jitter RMS	At 622.08MHz, with capacitive decoupling between VDD and GND. Over 10,000 cycles		11		ps
Period jitter peak-to-peak			45	49	
Accumulated jitter RMS	At 622.08MHz, with capacitive decoupling between VDD and GND. Over 1,000,000 cycles.		11		ps
Accumulated jitter peak-to-peak			24	27	
Random Jitter	"RJ" measured on Wavecrest SIA 3000		3		ps
Integrated jitter RMS at 622MHz	Integrated 12 kHz to 20 MHz		1.6	1.8	ps

5. Phase Noise Specifications

PARAMETERS	FREQUENCY	@10Hz	@100Hz	@1kHz	@10kHz	@100kHz	UNITS
Phase Noise relative to carrier	155.52MHz	-75	-95	-125	-140	-145	dBc/Hz
	622.08MHz	-75	-95	-110	-125	-120	

6. CMOS Electrical Specifications

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output drive current (High Drive)	I _{OH}	V _{OH} = V _{DD} -0.4V, V _{DD} =3.3V	30			mA
	I _{OL}	V _{OL} = 0.4V, V _{DD} = 3.3V	30			mA
Output drive current (Standard Drive)	I _{OH}	V _{OH} = V _{DD} -0.4V, V _{DD} =3.3V	10			mA
	I _{OL}	V _{OL} = 0.4V, V _{DD} = 3.3V	10			mA
Output Clock Rise/Fall Time (Standard Drive)		0.3V ~ 3.0V with 15 pF load		2.4		ns
Output Clock Rise/Fall Time (High Drive)		0.3V ~ 3.0V with 15 pF load		1.2		

* Note: High Drive CMOS is available on ABX2006 through DRIVSEL selector input on pin 12.

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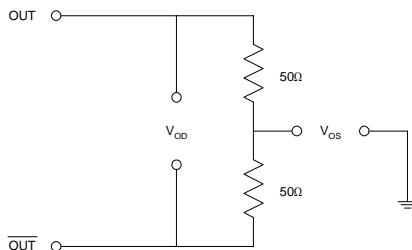
7. LVDS Electrical Characteristics

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Output Differential Voltage	V_{OD}	$R_L = 100 \Omega$ (see figure)	247	355	454	mV
V_{DD} Magnitude Change	ΔV_{OD}		-50		50	mV
Output High Voltage	V_{OH}			1.4	1.6	V
Output Low Voltage	V_{OL}		0.9	1.1		V
Offset Voltage	V_{OS}		1.125	1.2	1.375	V
Offset Magnitude Change	ΔV_{OS}		0	3	25	mV
Power-off Leakage	I_{OXD}	$V_{out} = V_{DD}$ or GND $V_{DD} = 0V$		± 1	± 10	μA
Output Short Circuit Current	I_{OSD}			-5.7	-8	mA

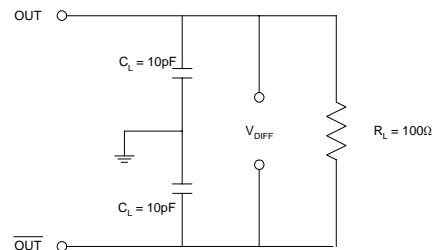
8. LVDS Switching Characteristics

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Differential Clock Rise Time	t_r	$R_L = 100 \Omega$ $C_L = 10 \text{ pF}$ (see figure)	0.2	0.7	1.0	ns
Differential Clock Fall Time	t_f		0.2	0.7	1.0	ns

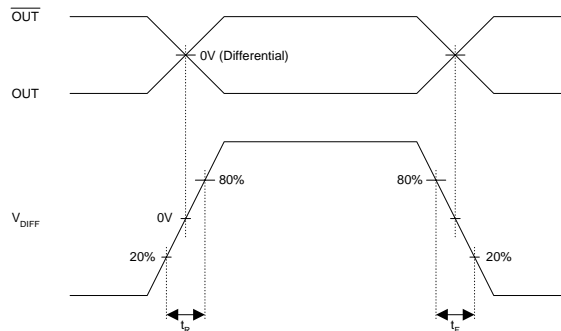
LVDS Levels Test Circuit



LVDS Switching Test Circuit



LVDS Transition Time Waveform



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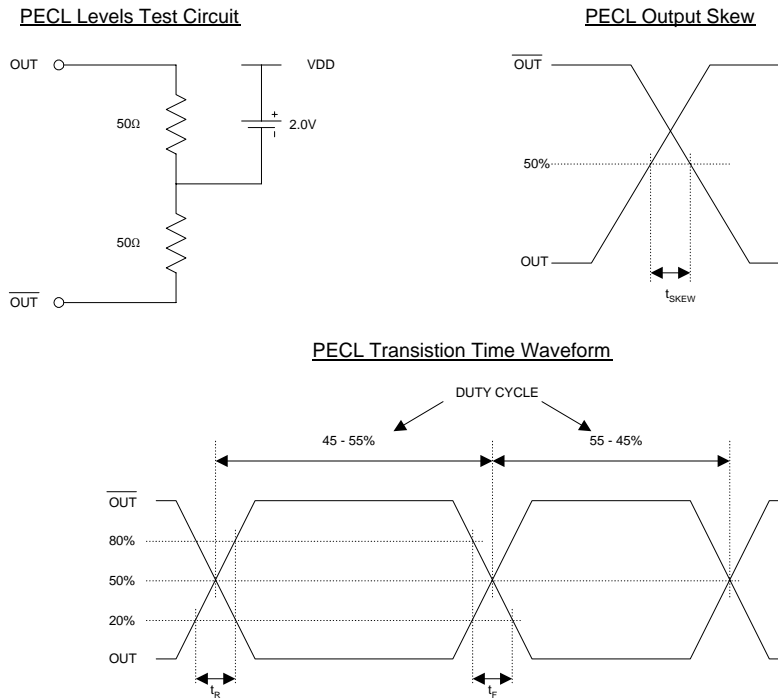
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9. PECL Electrical Characteristics

PARAMETERS	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
Output High Voltage	V_{OH}	$R_L = 50 \Omega$ to $(V_{DD} - 2V)$ (see figure)	$V_{DD} - 1.025$		V
Output Low Voltage	V_{OL}			$V_{DD} - 1.620$	V

19. PECL Switching Characteristics

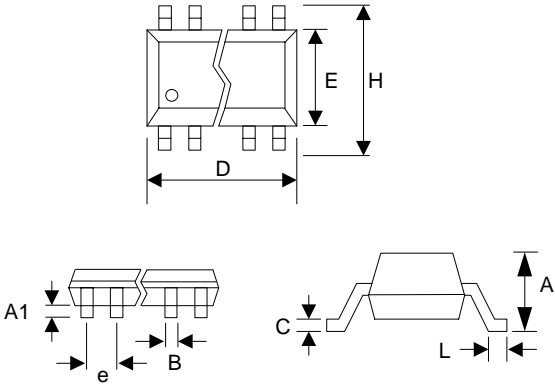
PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Clock Rise Time	t_r	@20/80% - PECL		0.6	1.5	ns
Clock Fall Time	t_f	@80/20% - PECL		0.5	1.5	ns



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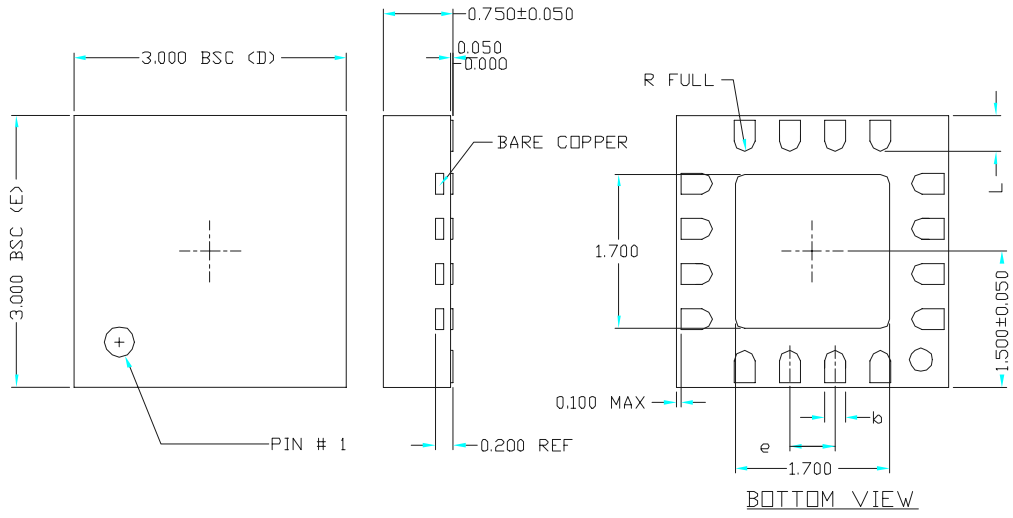
PACKAGE INFORMATION

16 PIN TSSOP (mm)		
Symbol	Min.	Max.
A	-	1.20
A1	0.05	0.15
B	0.19	0.30
C	0.09	0.20
D	4.90	5.10
E	4.30	4.50
H	6.40 BSC	
L	0.45	0.75
e	0.65 BSC	



3mm x 3mm, QFN

SYMBOL	16 LD		
	MIN	NOM	MAX
e	0.50 BSC		
b	0.18	0.23	0.30
L	0.30	0.40	0.50
ND	4		
NE	4		



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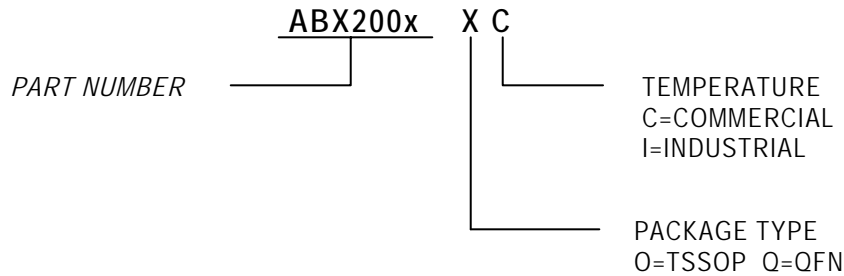
ORDERING INFORMATION

For part ordering, please contact our Sales Department:

30332 Esperanza., Rancho Santa Margarita, Ca 92688
Ph: 949-546-8000 Fax: 949-546-8001

PART NUMBER

The order number for this device is a combination of the following:
Device number, Package type and Operating temperature range



<u>Order Number</u>	<u>Marking</u>	<u>Package Option</u>
ABX2005OC	ABX2005OC	TSSOP – Tube
ABX2005OC-T	ABX2005OC	TSSOP – Tape & Reel
ABX2005QC	ABX2005QC	QFN – Tube
ABX2005QC-T	ABX2005QC	QFN – Tape & Reel
ABX2006QC	ABX2006QC	QFN – Tube
ABX2006QC-T	ABX2006QC	QFN – Tape & Reel
ABX2007OC	ABX2007OC	TSSOP – Tube
ABX2007OC-T	ABX2007OC	TSSOP – Tape & Reel
ABX2008OC	ABX2008OC	TSSOP – Tube
ABX2008OC-T	ABX2008OC	TSSOP – Tape & Reel
ABX2008QC	ABX2008QC	QFN – Tube
ABX2008QC-T	ABX2008QC	QFN – Tape & Reel
ABX2009OC	ABX2009OC	TSSOP – Tube
ABX2009OC-T	ABX2009OC	TSSOP – Tape & Reel
ABX2009QC	ABX2009QC	QFN – Tube
ABX2009QC-T	ABX2009QC	QFN – Tape & Reel

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